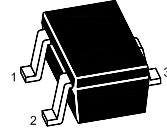


## PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications



1.Base 2.Emitter 3.Collector  
SOT-323 Plastic Package

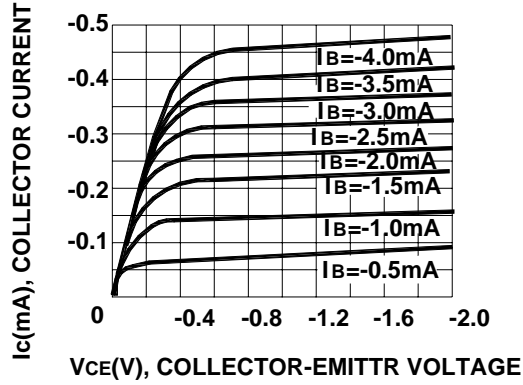
### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	25	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Peak Collector Current	$-I_{CM}$	1.5	A
Total Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{Stg}$	- 55 to + 150	$^\circ\text{C}$

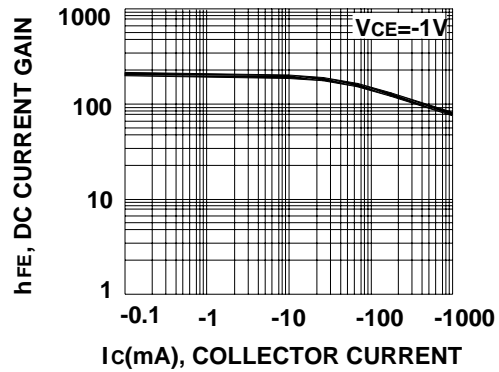
### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$ , $-I_C = 100\text{ mA}$ at $-V_{CE} = 1\text{ V}$ , $-I_C = 800\text{ mA}$	MMBT8550CW $h_{FE}$	100	250	-
	MMBT8550DW $h_{FE}$	160	400	-
	$h_{FE}$	40	-	-
Collector Base Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{CBO}$	40	-	V
Collector Emitter Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{CEO}$	25	-	V
Emitter Base Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{EBO}$	5	-	V
Collector Base Cutoff Current at $-V_{CB} = 40\text{ V}$	$-I_{CBO}$	-	100	nA
Collector Emitter Cutoff Current at $-V_{CE} = 20\text{ V}$	$-I_{CEO}$	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	100	nA
Collector Emitter Saturation Voltage at $-I_C = 800\text{ mA}$ , $-I_B = 80\text{ mA}$	$-V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_C = 800\text{ mA}$ , $-I_B = 80\text{ mA}$	$-V_{BE(sat)}$	-	1.2	V
Transition Frequency at $-V_{CE} = 10\text{ V}$ , $-I_C = 50\text{ mA}$ , $f = 30\text{ MHz}$	$f_T$	100	-	MHz

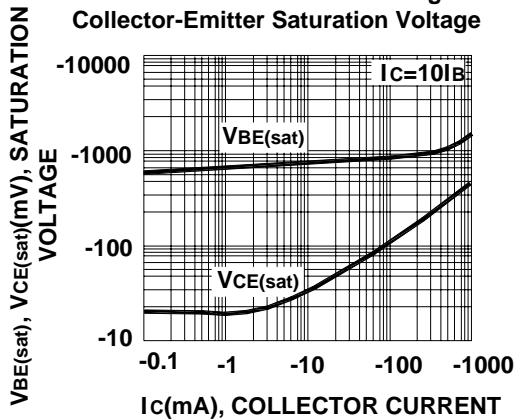
Static Characteristic



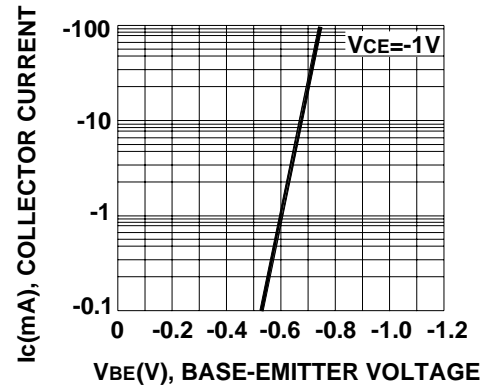
DC Current Gain



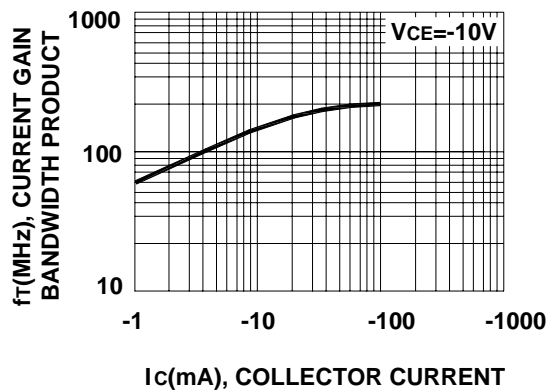
Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage



Base-Emitter On Voltage

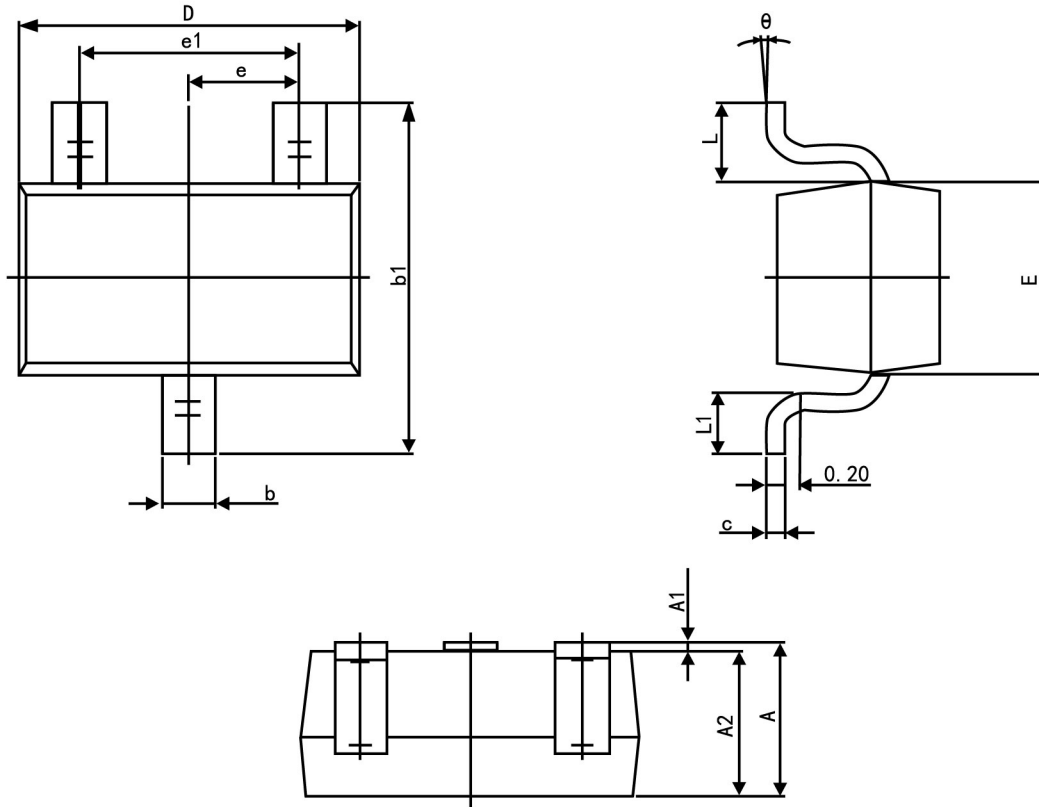


Current Gain Bandwidth Product





## SOT-323 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.200	0.400
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
θ	0°	8°